onsemi

N-Channel General-Purpose Amplifier

MMBFJ201, MMBFJ202

Description

This device is designed primarily for low level audio and general-purpose applications with high impedance signal sources. Sourced from process 52.

Applications

• These are Pb–Free Devices

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted) (Note 1, 2)

Symbol	Parameter	Value	Unit	
V _{DG}	Drain-Gate Voltage	40	V	
V _{GS}	Gate-Source Voltage	-40	V	
I _{GF}	Forward Gate Current	50	mA	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to 150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

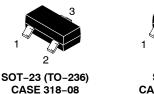
1. These ratings are based on a maximum junction temperature of 150°C.

 These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

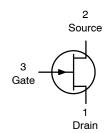
THERMAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Note 3)

Symbol	Parameter	neter Max	
PD	Total Device Dissipation	350	mW
	Derate Above 25°C	2.8	mW/°C
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

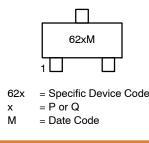
 Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm².



SOT-23 CASE 318BM







ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

MMBFJ201, MMBFJ202

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Test Condition		Max	Unit		
OFF CHARA	OFF CHARACTERISTICS							
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_{G} = -1.0 \ \mu A, \ V_{DS} = 0$		-40	-	V		
I _{GSS}	Gate Reverse Current	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0$	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0$		-100	pА		
V _{GS} (off)	Gate-Source Cut-Off Voltage	V _{DS} = 20 V, I _D = 10 nA	MMBFJ201	-0.3	-1.5	V		
			MMBFJ202	-0.8	-4.0			

ON CHARACTERISTICS

I _{DSS}	Zero-Gate Voltage Drain Current (Note 4)	$V_{DS} = 20 \text{ V}, \text{ I}_{GS} = 0$	MMBFJ201	0.2	1.0	mA
			MMBFJ202	0.9	4.5	

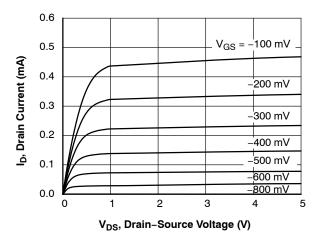
SMALL SIGNAL CHARACTERISTICS

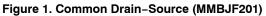
УFS	Forward Transfer Admittance	V _{DS} = 20 V, f = 1.0 kHz	MMBFJ201	500	μmhos
			MMBFJ202	1000	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse test: pulse width $\leq 300 \mu$ s, duty cycle $\leq 2\%$.

MMBFJ201, MMBFJ202

TYPICAL PERFORMANCE CHARACTERISTICS





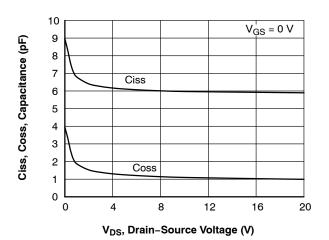


Figure 3. Capacitance vs. Voltage (MMBJF201)

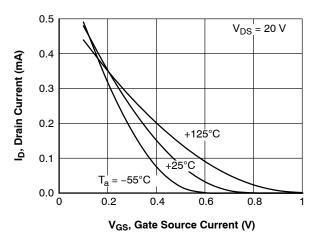


Figure 5. Transfer Characteristics (MMBFJ201)

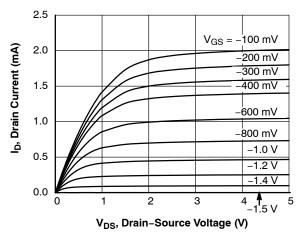


Figure 2. Common Drain-Source (MMBJF202)

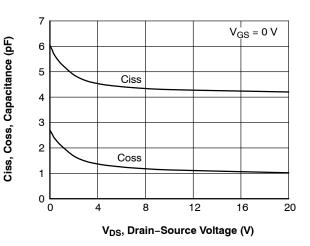
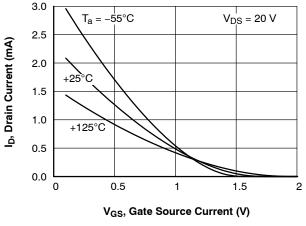


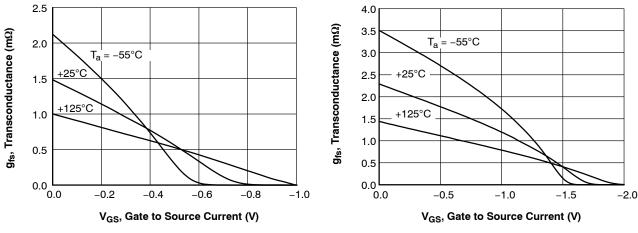
Figure 4. Capacitance vs. Voltage (MMBJF202)





MMBFJ201, MMBFJ202

TYPICAL PERFORMANCE CHARACTERISTICS (continued)







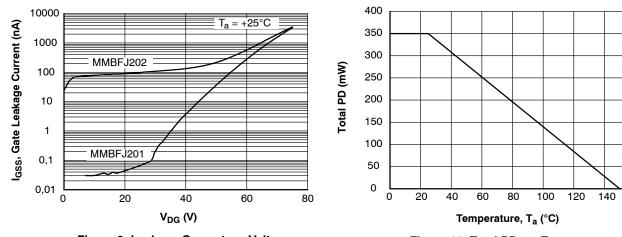


Figure 9. Leakage Current vs. Voltage



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ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping [†]
MMBFJ201	62P	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBFJ202	62Q	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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TOP VIEW

SIDE VIEW

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DETAIL A

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SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

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DETAIL A

END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	IETERS			INCHES	
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*





XXX = Specific Device Code

M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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